

# DATA SHEET

For a complete data sheet, please also download:

- The IC04 LOCMOS HE4000B Logic Family Specifications HEF, HEC
- The IC04 LOCMOS HE4000B Logic Package Outlines/Information HEF, HEC

## **HEF4069UB** **gates** **Hex inverter**

Product specification  
File under Integrated Circuits, IC04

January 1995

# Hex inverter

# HEF4069UB gates

### DESCRIPTION

The HEF4069UB is a general purpose hex inverter. Each of the six inverters is a single stage.

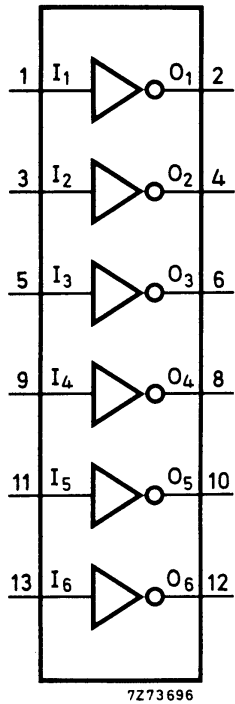


Fig.1 Functional diagram.

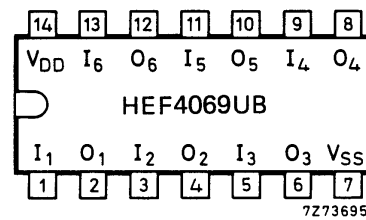


Fig.2 Pinning diagram.

- HEF4069UBP(N): 14-lead DIL; plastic (SOT27-1)
- HEF4069UBD(F): 14-lead DIL; ceramic (cerdip) (SOT73)
- HEF4069UBT(D): 14-lead SO; plastic (SOT108-1)
- ( ): Package Designator North America

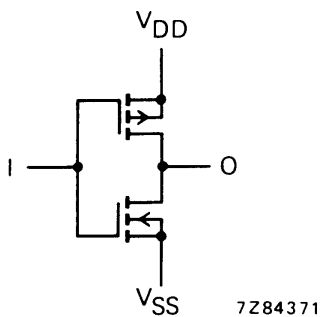


Fig.3 Schematic diagram (one inverter).

### FAMILY DATA, I<sub>DD</sub> LIMITS category GATES

See Family Specifications for V<sub>IH</sub>/V<sub>IL</sub> unbuffered stages

Hex inverter

HEF4069UB  
gates

**AC CHARACTERISTICS**

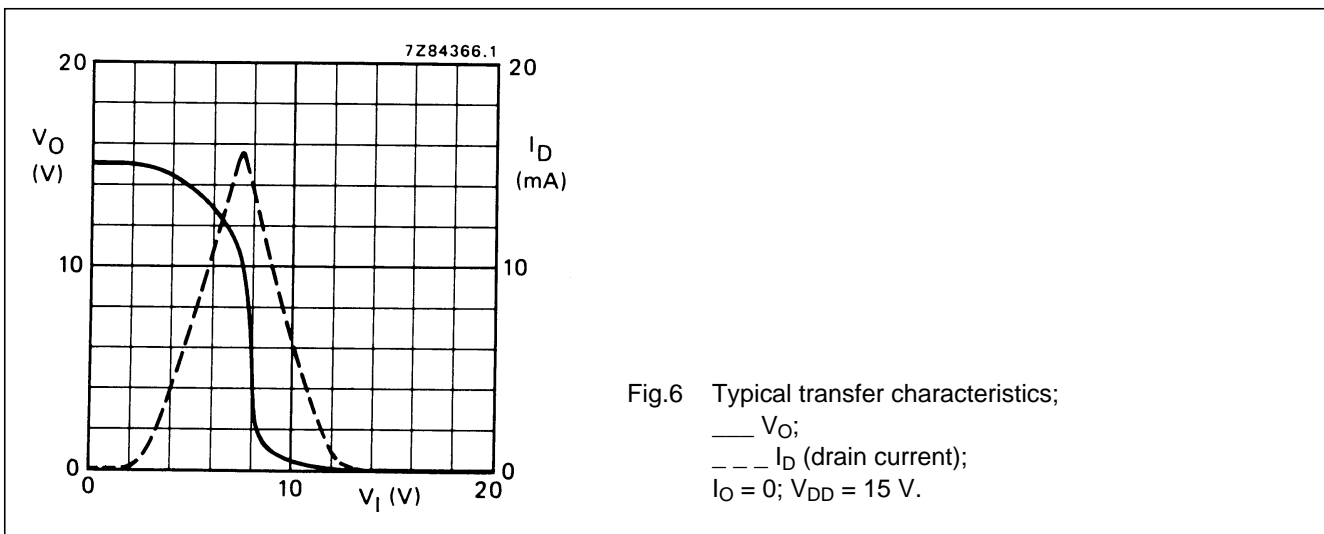
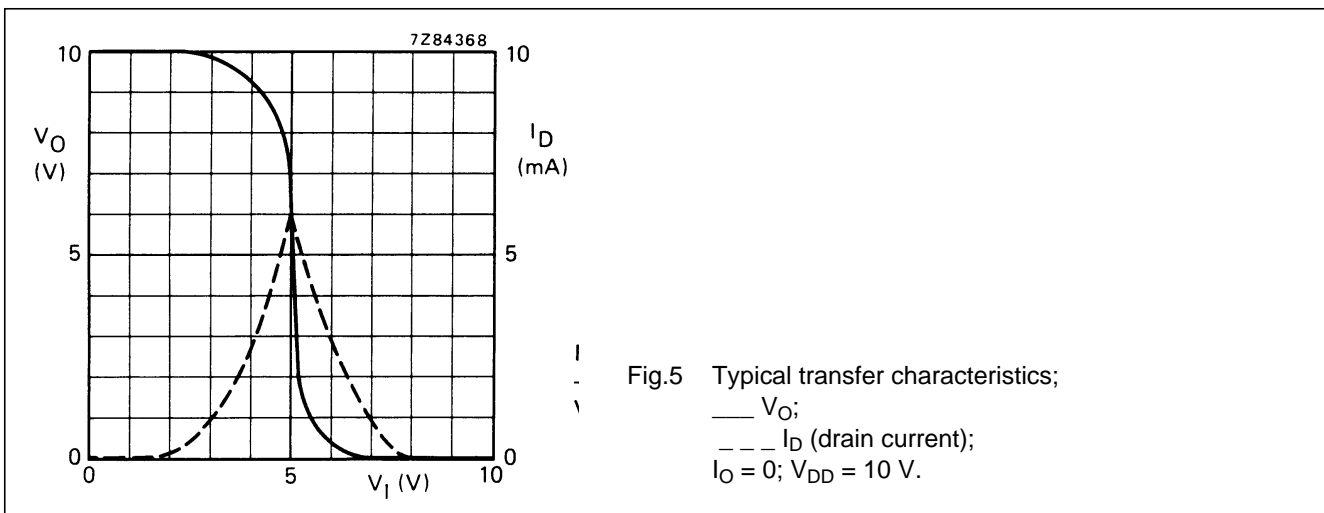
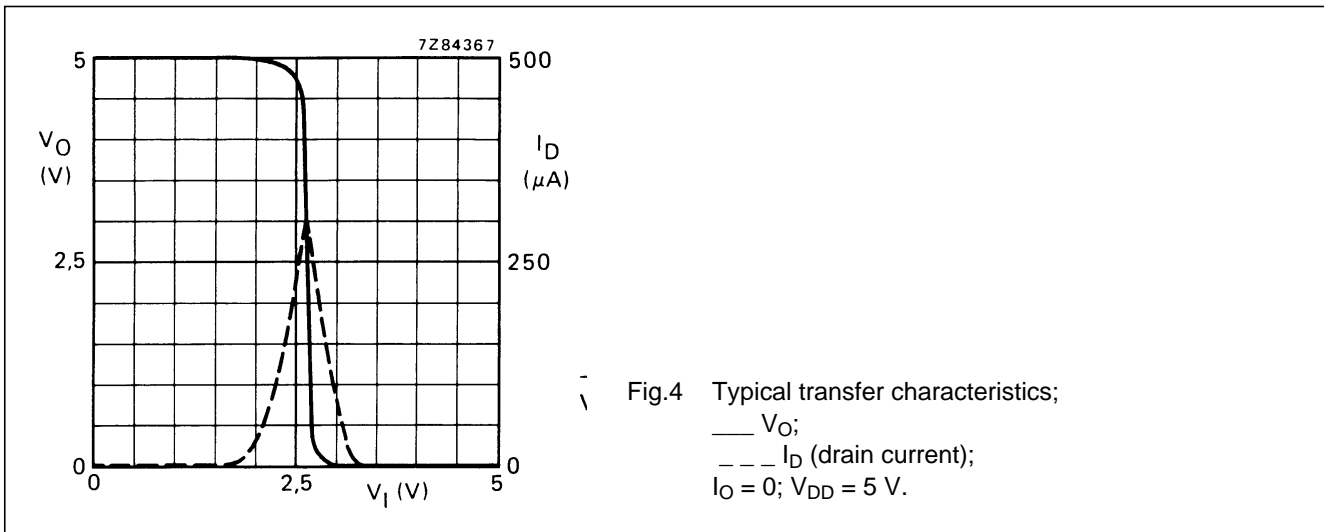
$V_{SS} = 0\text{ V}$ ;  $T_{amb} = 25\text{ }^\circ\text{C}$ ;  $C_L = 50\text{ pF}$ ; input transition times  $\leq 20\text{ ns}$

	$V_{DD}$ V	SYMBOL	TYP.	MAX.	TYPICAL EXTRAPOLATION FORMULA
Propagation delays $I_n \rightarrow O_n$ HIGH to LOW  LOW to HIGH	5	$t_{PHL}$	45	90 ns	$18\text{ ns} + (0,55\text{ ns/pF}) C_L$
	10		20	40 ns	$9\text{ ns} + (0,23\text{ ns/pF}) C_L$
	15		15	25 ns	$7\text{ ns} + (0,16\text{ ns/pF}) C_L$
	5	$t_{PLH}$	40	80 ns	$13\text{ ns} + (0,55\text{ ns/pF}) C_L$
	10		20	40 ns	$9\text{ ns} + (0,23\text{ ns/pF}) C_L$
	15		15	30 ns	$7\text{ ns} + (0,16\text{ ns/pF}) C_L$
Output transition times HIGH to LOW  LOW to HIGH	5	$t_{THL}$	60	120 ns	$10\text{ ns} + (1,0\text{ ns/pF}) C_L$
	10		30	60 ns	$9\text{ ns} + (0,42\text{ ns/pF}) C_L$
	15		20	40 ns	$6\text{ ns} + (0,28\text{ ns/pF}) C_L$
	5	$t_{TLH}$	60	120 ns	$10\text{ ns} + (1,0\text{ ns/pF}) C_L$
	10		30	60 ns	$9\text{ ns} + (0,42\text{ ns/pF}) C_L$
	15		20	40 ns	$6\text{ ns} + (0,28\text{ ns/pF}) C_L$

	$V_{DD}$ V	TYPICAL FORMULA FOR P ( $\mu\text{W}$ )	
Dynamic power dissipation per package (P)	5	$600 f_i + \sum (f_o C_L) \times V_{DD}^2$	where $f_i$ = input freq. (MHz) $f_o$ = output freq. (MHz) $C_L$ = load capacitance (pF) $\sum (f_o C_L)$ = sum of outputs $V_{DD}$ = supply voltage (V)
	10	$4\ 000 f_i + \sum (f_o C_L) \times V_{DD}^2$	
	15	$22\ 000 f_i + \sum (f_o C_L) \times V_{DD}^2$	

Hex inverter

HEF4069UB  
gates



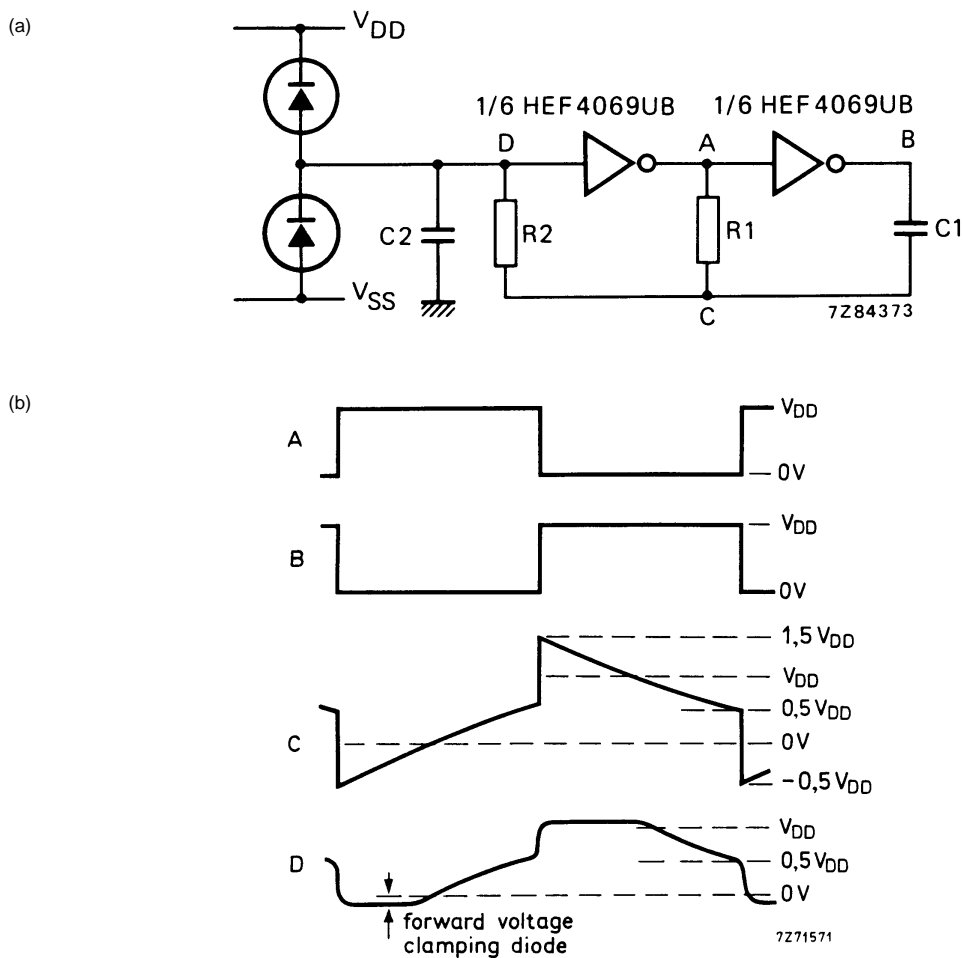
Hex inverter

HEF4069UB  
gates

APPLICATION INFORMATION

Some examples of applications for the HEF4069UB are shown below.

In Fig.7 an astable relaxation oscillator is given. The oscillation frequency is mainly determined by R1C1, provided  $R1 \ll R2$  and  $R2C2 \ll R1C1$ .



The function of R2 is to minimize the influence of the forward voltage across the protection diodes on the frequency; C2 is a stray (parasitic) capacitance. The period  $T_p$  is given by  $T_p = T_1 + T_2$ , in which

$$T_1 = R1C1 \ln \frac{V_{DD} + V_{ST}}{V_{ST}} \text{ and } T_2 = R1C1 \ln \frac{2V_{DD} - V_{ST}}{V_{DD} - V_{ST}} \text{ where}$$

$V_{ST}$  is the signal threshold level of the inverter. The period is fairly independent of  $V_{DD}$ ,  $V_{ST}$  and temperature. The duty factor, however, is influenced by  $V_{ST}$ .

Fig.7 (a) Astable relaxation oscillator using two HEF4069UB inverters; the diodes may be BAW62; C2 is a parasitic capacitance. (b) Waveforms at the points marked A, B, C and D in the circuit diagram.

Hex inverter

HEF4069UB  
gates

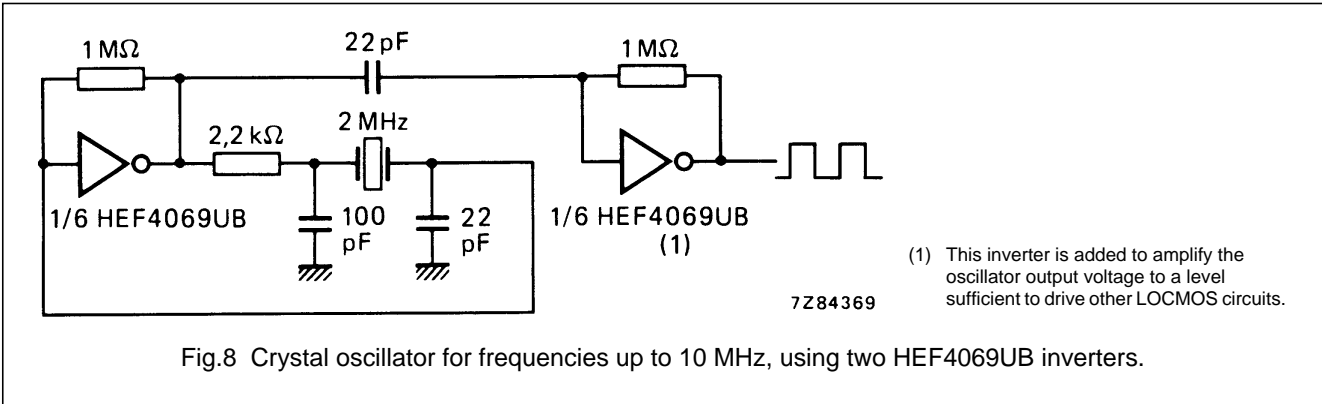


Fig.8 Crystal oscillator for frequencies up to 10 MHz, using two HEF4069UB inverters.

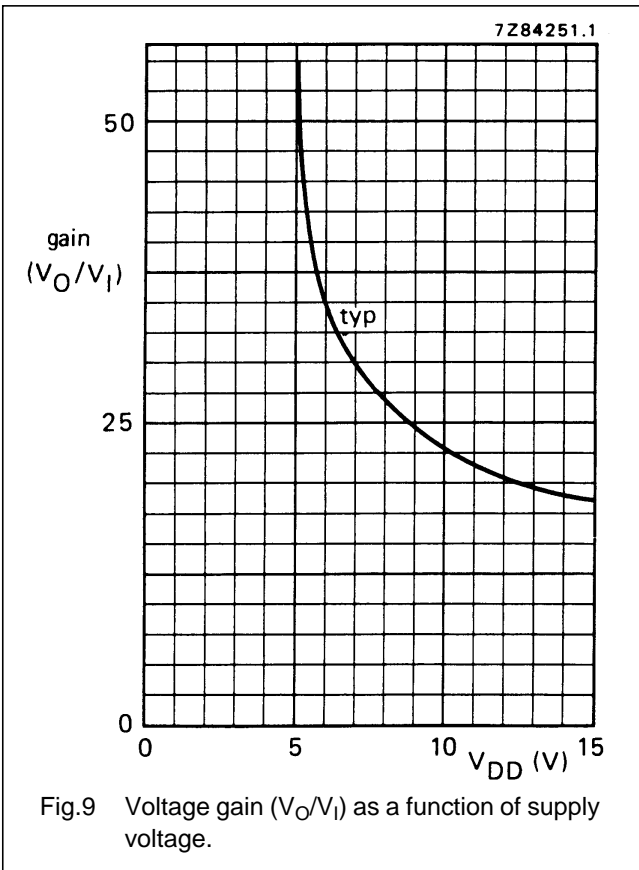


Fig.9 Voltage gain ( $V_O/V_I$ ) as a function of supply voltage.

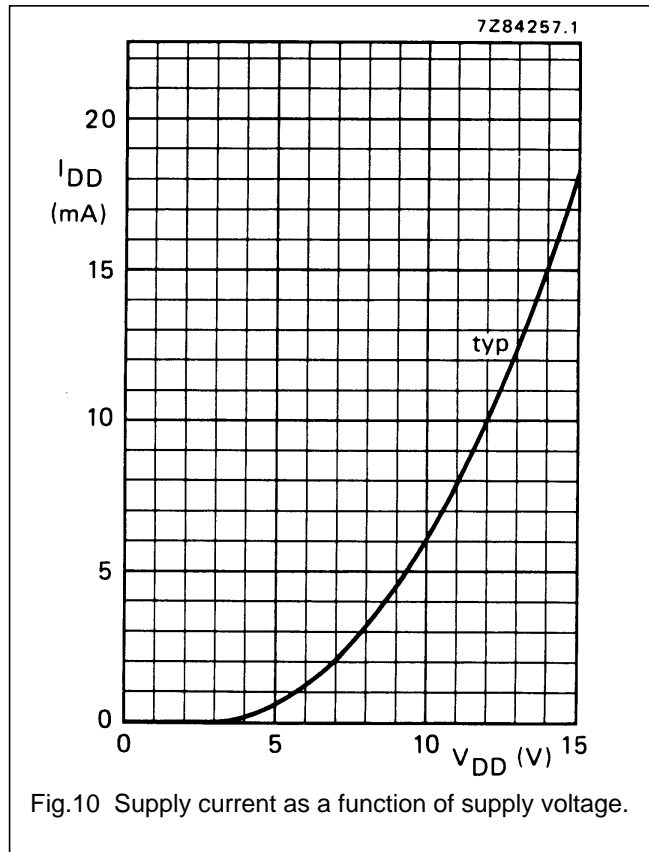


Fig.10 Supply current as a function of supply voltage.

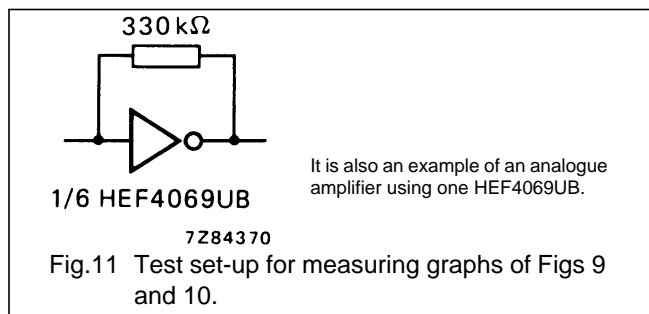


Fig.11 Test set-up for measuring graphs of Figs 9 and 10.

Hex inverter

HEF4069UB  
gates

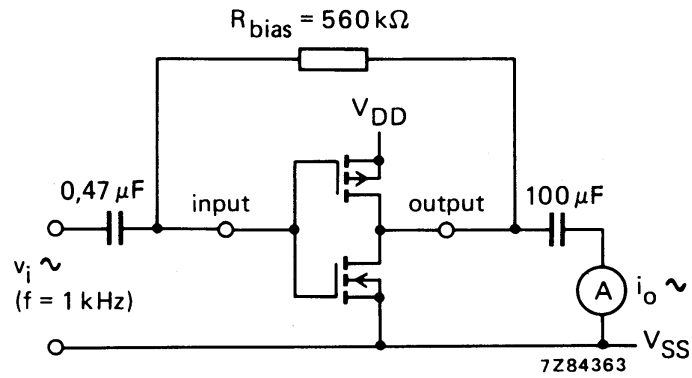


Fig.12 Test set-up for measuring forward transconductance  $g_{fs} = di_o/dv_i$  at  $v_o$  is constant (see also graph Fig.13).

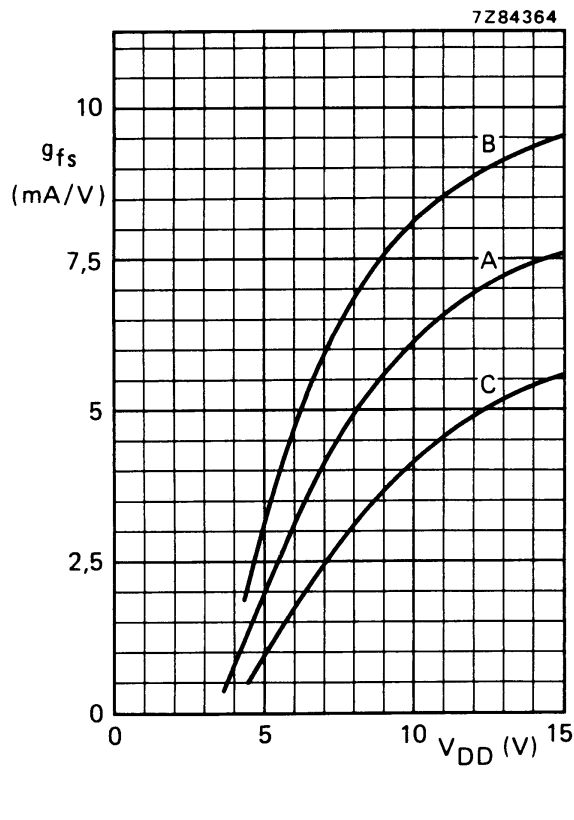


Fig.13 Typical forward transconductance  $g_{fs}$  as a function of the supply voltage at  $T_{amb} = 25\text{ }^{\circ}\text{C}$ .